Shoou-Jinn Chang

List of Publications by Year
in descending order

284	6,141	87888 38	110387 64
papers	citations	h-index	g-index

284	284	284	6034
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	The study of humidity sensor based on Li-doped ZnO nanorods by hydrothermal method. Microsystem Technologies, 2022, 28, 423-427.	2.0	4
2	Aluminum-doped zinc oxide nanorods and methyl alcohol gas sensor application. Microsystem Technologies, 2022, 28, 377-382.	2.0	6
3	A Room-Temperature TiO₂-based Ammonia Gas Sensor with Three-Dimensional Through-Silicon-Via Structure. ECS Journal of Solid State Science and Technology, 2022, 11, 067002.	1.8	6
4	The Characteristics of Aluminum-Gallium-Zinc-Oxide Ultraviolet Phototransistors by Co-Sputtering Method. Electronics (Switzerland), 2021, 10, 631.	3.1	2
5	Stability-Enhanced Resistive Random-Access Memory via Stacked In_xGa_{1â€“x}O by the RF Sputtering Method. ACS Omega, 2021, 6, 10691-10697.	3.5	4
6	High Response of Ethanol Gas Sensor Based on NiO-Doped Apple Pectin by the Solution Process. Coatings, 2021, 11, 1073.	2.6	1
7	Photoresponses of Zinc Tin Oxide Thin-Film Transistor. Journal of Nanoscience and Nanotechnology, 2020, 20, 1704-1708.	0.9	7
8	Voltage-Tunable UVCâ€“UVB Dual-Band Metalâ€“Semiconductorâ€“Metal Photodetector Based on Ga2O3/MgZnO Heterostructure by RF Sputtering. Coatings, 2020, 10, 994.	2.6	6
9	Fabrication of Silicon Dioxide by Photo-Chemical Vapor Deposition to Decrease Detector Current of ZnO Ultraviolet Photodetectors. ACS Omega, 2020, 5, 27566-27571.	3.5	3
10	Investigation of Conductive Mechanism of Amorphous IGO Resistive Random-Access Memory with Different Top Electrode Metal. Coatings, 2020, 10, 504.	2.6	4
11	An Amorphous (Al0.12Ga0.88)2O3 Deep Ultraviolet Photodetector. IEEE Photonics Journal, 2020, 12, 1-8.	2.0	2
12	Polycrystalline Inâ€“Gaâ€“O Thin-Film Transistors Coupled With a Nitrogen Doping Technique for High-Performance UV Detectors. IEEE Transactions on Electron Devices, 2020, 67, 140-145.	3.0	3
13	Corrosion-induced degradation and its mechanism study of Cuâ€“Al interface for Cu-wire bonding under HAST conditions. Journal of Alloys and Compounds, 2020, 825, 154046.	5.5	13
14	Investigation of nitrogen doping effects on light-induced oxygen vacancy ionization and oxygen desorption in c-IGO TFTs. Materials Research Express, 2019, 6, 106445.	1.6	3
15	Fast Detection and Flexible Microfluidic pH Sensors Based on Al-Doped ZnO Nanosheets with a Novel Morphology. ACS Omega, 2019, 4, 19847-19855.	3.5	27
16	Ultraviolet/Visible Photodetectors Based on pâ€“n NiO/ZnO Nanowires Decorated with Pd Nanoparticles. ACS Applied Nano Materials, 2019, 2, 6343-6351.	5.0	36
17	A Novel Transparent Microwave Thin Film Coating Technique Applied to Dual-Band Antennas. Electronic Materials Letters, 2019, 15, 680-685.	2.2	2
18	The Effect of Oxygen Partial Pressure and Annealing Process on the Characteristics of ZnGa₂O₄ÂMSM UV Photodetector. ECS Journal of Solid State Science and Technology, 2019, 8, Q3213-Q3216.	1.8	19

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19	Integration of bandgap-engineered double-stacked channel layers with nitrogen doping for high-performance InGaO TFTs. Applied Physics Letters, 2019, 114, .	3.3	20
20	Indium Aluminum Zinc Oxide Thin Film Transistor With Al₂O₃ Dielectric for UV Sensing. IEEE Photonics Technology Letters, 2019, 31, 1005-1008.	2.5	7
21	Indium Gallium Oxide Thin Film Transistor for Two-Stage UV Sensor Application. ECS Journal of Solid State Science and Technology, 2019, 8, Q3140-Q3143.	1.8	15
22	Stability Improvement of Nitrogen Doping on IGO TFTs under Positive Gate Bias Stress and Hysteresis Test. ECS Journal of Solid State Science and Technology, 2019, 8, Q3034-Q3040.	1.8	10
23	Cu-Al interfacial formation and kinetic growth behavior during HTS reliability test. Journal of Materials Processing Technology, 2019, 267, 90-102.	6.3	22
24	Visible Illumination Enhanced Nonenzymatic Glucose Photobiosensor Based on TiO₂ Nanorods Decorated With Au Nanoparticles. IEEE Transactions on Biomedical Engineering, 2018, 65, 2052-2057.	4.2	5
25	High Density Novel Porous ZnO Nanosheets Based on a Microheater Chip for Ozone Sensors. IEEE Sensors Journal, 2018, 18, 5559-5565.	4.7	26
26	Amorphous Indium Titanium Zinc Oxide Thin Film Transistor and Impact of Gate Dielectrics on Its Photo-Electrical Properties. ECS Journal of Solid State Science and Technology, 2018, 7, Q3049-Q3053.	1.8	3
27	Photo-Electrical Properties of MgZnO Thin-Film Transistors With High- ${k}$ Dielectrics. IEEE Photonics Technology Letters, 2018, 30, 59-62.	2.5	17
28	Influence of oxygen on the performance of indium titanium zinc oxide UV sensors fabricated via RF sputtering. Materials Science in Semiconductor Processing, 2018, 74, 297-302.	4.0	8
29	Photoresponses of Gallium Zinc Tin Oxide Thin-Film Transistors Fabricated by Cosputtering Method. , 2018, 2, 1-4.		1
30	UV-Enhanced 2-D Nanostructured ZnO Field Emitter With Adsorbed Pt Nanoparticles. IEEE Electron Device Letters, 2018, 39, 1932-1935.	3.9	6
31	High Sensitivity of NO Gas Sensors Based on Novel Ag-Doped ZnO Nanoflowers Enhanced with a UV Light-Emitting Diode. ACS Omega, 2018, 3, 13798-13807.	3.5	92
32	3D RGB Light Emitting Diodes Prepared by Through Silicon Via Technology. ECS Journal of Solid State Science and Technology, 2018, 7, R156-R159.	1.8	3
33	Effect of Oxygen Vacancy Ratio on a GaZTO Solar-Blind Photodetector. Coatings, 2018, 8, 293.	2.6	14
34	Electrical Properties of Indium Aluminum Zinc Oxide Thin Film Transistors. Journal of Electronic Materials, 2018, 47, 6923-6928.	2.2	17
35	Highly Stable Ultrathin TiO₂Based Resistive Random Access Memory with Low Operation Voltage. ECS Journal of Solid State Science and Technology, 2018, 7, Q3183-Q3188.	1.8	24
36	Highly stable ITO/Zn2TiO4/Pt resistive random access memory and its application in two-bit-per-cell. RSC Advances, 2018, 8, 17622-17628.	3.6	12

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37	Effect of different partial pressure on Ga-doped ZnO UV photodetectors by RF sputtering. , 2018, , .		0
38	Communicationâ€"Diffusion Break-Assisted Programming Mode for Active Electrically Programmable Fuse. ECS Journal of Solid State Science and Technology, 2018, 7, Q109-Q111.	1.8	3
39	Design of Dual-Band Transparent Antenna by Using Nano-Structured Thin Film Coating Technology. , 2018, , .		2
40	Influence of Annealing Ambience on TiO₂Film Ultraviolet Photodetector. ECS Journal of Solid State Science and Technology, 2017, 6, Q3056-Q3060.	1.8	5
41	Transparent gas senor and photodetector based on Al doped ZnO nanowires synthesized on glass substrate. Ceramics International, 2017, 43, 5434-5440.	4.8	36
42	Tunable UV- and Visible-Light Photoresponse Based on p-ZnO Nanostructures/n-ZnO/Glass Peppered with Au Nanoparticles. ACS Applied Materials & Interfaces, 2017, 9, 14935-14944.	8.0	57
43	Nonenzymatic Glucose Sensor Based on Au/ZnO Coreâ€"Shell Nanostructures Decorated with Au Nanoparticles and Enhanced with Blue and Green Light. Journal of Physical Chemistry B, 2017, 121, 2931-2941.	2.6	27
44	Through-Silicon via Submount for Flip-Chip LEDs. ECS Journal of Solid State Science and Technology, 2017, 6, R159-R162.	1.8	5
45	High Responsivity MgZnO Ultraviolet Thin-Film Phototransistor Developed Using Radio Frequency Sputtering. Materials, 2017, 10, 126.	2.9	23
46	Oxygen Partial Pressure Impact on Characteristics of Indium Titanium Zinc Oxide Thin Film Transistor Fabricated via RF Sputtering. Nanomaterials, 2017, 7, 156.	4.1	15
47	High efficiency transparent digital television antenna based on nano-structured thin film coating technology. , 2017, , .		2
48	Enhanced Photoluminescent Properties and Crystalline Morphology of LiBaPO4:Tm3+ Phosphor through Microwave Sintering Method. Materials, 2016, 9, 356.	2.9	7
49	White-Light Emission From GaN-Based TJ LEDs Coated With Red Phosphor. IEEE Electron Device Letters, 2016, 37, 1150-1153.	3.9	11
50	A new high transmittance dipole antenna. , 2016, , .		1
51	Fabrication and sulfurization of Cu2SnS3 thin films with tuning the concentration of Cu-Sn-S precursor ink. Applied Surface Science, 2016, 388, 71-76.	6.1	13
52	Effect of different alkali carbonate on the microstructure and photoluminescent properties of YInGe2O7:Eu3+ phosphors. Journal of Materials Science: Materials in Electronics, 2016, 27, 2963-2967.	2.2	5
53	A low-temperature ZnO nanowire ethanol gas sensor prepared on plastic substrate. Materials Research Express, 2016, 3, 095002.	1.6	15
54	A 3-D ZnO-Nanowire Smart Photo Sensor Prepared With Through Silicon via Technology. IEEE Transactions on Electron Devices, 2016, 63, 3562-3566.	3.0	5

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55	Novel top-down Cu filling of through silicon via (TSV) in 3-D integration. , 2016, , .		0
56	Characterization of High Mg Content MgZnO Ultraviolet Photodetectors with Noise Properties. ECS Journal of Solid State Science and Technology, 2016, 5, Q191-Q194.	1.8	6
57	Transparent ZnO-nanowire-based device for UV light detection and ethanol gas sensing on c-Si solar cell. RSC Advances, 2016, 6, 11146-11150.	3.6	35
58	Near-Infrared Multichannel Filter in a Finite Semiconductor Metamaterial Photonic Crystal. IEEE Photonics Journal, 2016, 8, 1-9.	2.0	0
59	Improving FET Properties of Semiconducting Single-Walled Carbon Nanotubes by Selective Extraction. IEEE Transactions on Electron Devices, 2016, 63, 1749-1753.	3.0	0
60	Carbon Nanotube Thin Films Functionalized via Loading of Au Nanoclusters for Flexible Gas Sensors Devices. IEEE Transactions on Electron Devices, 2016, 63, 476-480.	3.0	29
61	Investigation of low-frequency noise of 28-nm technology process of high-k/metal gate p-MOSFETs with fluorine incorporation. Solid-State Electronics, 2016, 115, 7-11.	1.4	2
62	Bipolar Resistive Switching Characteristics of TaO₂ RRAM. Science of Advanced Materials, 2016, 8, 1108-1111.	0.7	2
63	High Responsivity Mg_xZn_{1â^'x}O Film UV Photodetector Grown by RF Sputtering. IEEE Photonics Technology Letters, 2015, 27, 978-981.	2.5	18
64	Si-Based MOSFET and Thin Film Transistor Prepared via Hot Wire Implantation Doping Technique. IEEE Electron Device Letters, 2015, 36, 93-95.	3.9	4
65	Amorphous Indiumâ€“Galliumâ€“Oxide UV Photodetectors. IEEE Photonics Technology Letters, 2015, 27, 2083-2086.	2.5	41
66	GaN-based Dual-Color Light-Emitting Diodes With a Hybrid Tunnel Junction Structure. Journal of Display Technology, 2015, , 1-1.	1.2	5
67	Structural and Raman properties of silver-doped ZnO nanorod arrays using electrically induced crystallization process. Materials Research Bulletin, 2015, 64, 274-278.	5.2	11
68	Electrochromic Device Integrated With GaInP/GaAs/Ge Triple-Junction Solar Cell. IEEE Electron Device Letters, 2015, 36, 207-209.	3.9	7
69	GaN-Based Multiquantum Well Light-Emitting Diodes With Tunnel-Junction-Cascaded Active Regions. IEEE Electron Device Letters, 2015, 36, 366-368.	3.9	31
70	Bandgap-Engineered in Indiumâ€“Galliumâ€“Oxide Ultraviolet Phototransistors. IEEE Photonics Technology Letters, 2015, 27, 915-918.	2.5	41
71	Terahertz Negative Refraction in a High-Temperature Superconducting Material. IEEE Transactions on Terahertz Science and Technology, 2015, 5, 230-235.	3.1	2
72	Cascaded GaN Light-Emitting Diodes With Hybrid Tunnel Junction Layers. IEEE Journal of Quantum Electronics, 2015, 51, 1-5.	1.9	16

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73	GaN MSM UV Photodetector With Sputtered AlN Nucleation Layer. IEEE Sensors Journal, 2015, 15, 4743-4748.	4.7	37
74	UV Enhanced Field Emission Properties of Ga-Doped ZnO Nanosheets. IEEE Transactions on Electron Devices, 2015, 62, 2033-2037.	3.0	12
75	Electron field emission enhancement of hybrid Cu/CuO nanowires fabricated by rapid thermal reduction of CuO nanowires. RSC Advances, 2015, 5, 54220-54224.	3.6	11
76	Conversion Efficiency Improvement of InGaN/GaN Multiple-Quantum-Well Solar Cells With <italic>Ex Situ</italic> AlN Nucleation Layer. IEEE Transactions on Electron Devices, 2015, 62, 1473-1477.	3.0	7
77	Bipolar Ni/ZnO/HfO2/Ni RRAM with multilevel characteristic by different reset bias. Materials Science in Semiconductor Processing, 2015, 35, 30-33.	4.0	28
78	Effects of last barrier thickness on the hotâ€“cold factor of GaN-based light-emitting diodes. Journal of Photonics for Energy, 2015, 5, 057602.	1.3	0
79	Effects of microcell layout on the performance of GaN-based high-voltage light-emitting diodes. Journal of Photonics for Energy, 2015, 5, 057605.	1.3	6
80	GaN-Based Power Flip-Chip LEDs With SILAR and Hydrothermal ZnO Nanorods. IEEE Journal of Selected Topics in Quantum Electronics, 2015, 21, 431-435.	2.9	3
81	CO₂Gas Sensors Based on Carbon Nanotube Thin Films Using a Simple Transfer Method on Flexible Substrate. IEEE Sensors Journal, 2015, 15, 7017-7020.	4.7	41
82	Enhancement in the structure quality of ZnO nanorods by diluted Co dopants: Analyses via optical second harmonic generation. Journal of Applied Physics, 2015, 117, .	2.5	11
83	Ga-Doped ZnO Nanosheet Structure-Based Ultraviolet Photodetector by Low-Temperature Aqueous Solution Method. IEEE Transactions on Electron Devices, 2015, 62, 2924-2927.	3.0	30
84	Two-bit-per-cell resistive switching memory device with a Ti/MgZnO/Pt structure. RSC Advances, 2015, 5, 88166-88170.	3.6	11
85	UV Enhanced Field Emission Properties of ZnO Nanosheets With Different NaOH Concentration. IEEE Nanotechnology Magazine, 2015, 14, 776-781.	2.0	11
86	Effect of Solvent Chelating on Crystal Growth Mechanism of CZTSe Nanoink in Polyetheramine. IEEE Nanotechnology Magazine, 2015, 14, 896-903.	2.0	1
87	Three-dimensional ZnO nanostructure photodetector prepared with through silicon via technology. Optics Letters, 2015, 40, 2878.	3.3	7
88	Improved high-k stacks with chemical oxide interfacial layer by DPN/PNA treatment. Current Applied Physics, 2015, 15, 180-182.	2.4	0
89	A Tri-Band Bandpass Filter With Wide Stopband Using Asymmetric Stub-Loaded Resonators. IEEE Microwave and Wireless Components Letters, 2015, 25, 19-21.	3.2	53
90	Light Emitting Diodes. Topics in Applied Physics, 2015, , 179-234.	0.8	1

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91	Asymmetric resistive switching characteristics of In2O3:SiO2 cosputtered thin film memories. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2014, 32, 020603.	1.2	6
92	Trap properties of high-k/metal gate pMOSFETs with aluminum ion implantation by random telegraph noise and 1/fnoise measurements. Japanese Journal of Applied Physics, 2014, 53, 04EC14.	1.5	1
93	Enhanced Field Emission Properties of Ga-Doped ZnO Nanosheets by using an Aqueous Solution at Room Temperature. IEEE Transactions on Electron Devices, 2014, 61, 4192-4196.	3.0	15
94	GaN-Based LEDs With Hot/Cold Factor Improved by the Electron Blocking Layer. Journal of Display Technology, 2014, 10, 1078-1082.	1.2	5
95	Frequency Response of a Ferroelectric Material in Double-Negative Region. IEEE Photonics Journal, 2014, 6, 1-11.	2.0	0
96	Synthesis and characterization of CZTSe nanoinks using polyetheramine as solvent. Optical Materials Express, 2014, 4, 1593.	3.0	6
97	Analysis of photonic bandgap structure for a polaritonic photonic crystal in negative-index region. Journal of the Optical Society of America B: Optical Physics, 2014, 31, 1730.	2.1	1
98	Investigation of trap properties in high-k/metal gate p-type metal-oxide-semiconductor field-effect-transistors with aluminum ion implantation using random telegraph noise analysis. Applied Physics Letters, 2014, 105, 062109.	3.3	1
99	Doped ZnO 1D Nanostructures: Synthesis, Properties, and Photodetector Application. Small, 2014, 10, 4562-4585.	10.0	166
100	UV Enhanced Field Emission Performance of Mg-Doped ZnO Nanorods. IEEE Transactions on Electron Devices, 2014, 61, 1541-1545.	3.0	26
101	A high selectivity and wide stopband UWB bandpass filter using asymmetric SIRs with splitâ€end. Microwave and Optical Technology Letters, 2014, 56, 1353-1356.	1.4	1
102	Probing Surface Structure Quality of ZnO Nanorods by Second Harmonic Generation. IEEE Photonics Technology Letters, 2014, 26, 789-792.	2.5	8
103	ALD TiN Barrier Metal for pMOS Devices With a Chemical Oxide Interfacial Layer for 20-nm Technology Node. IEEE Electron Device Letters, 2014, 35, 306-308.	3.9	8
104	ZnO-Based Ultraviolet Photodetectors With Novel Nanosheet Structures. IEEE Nanotechnology Magazine, 2014, 13, 238-244.	2.0	31
105	Visible-Blind Photodetectors With Mg-Doped ZnO Nanorods. IEEE Photonics Technology Letters, 2014, 26, 645-648.	2.5	34
106	GaN-Based LEDs With Rough Surface and Selective KOH Etching. Journal of Display Technology, 2014, 10, 27-32.	1.2	8
107	See-Through Si Thin-Film Tandem Solar Cell Module With Hardener. IEEE Journal of Photovoltaics, 2014, 4, 1013-1017.	2.5	3
108	Performance Enhancement of High-Current-Injected Electrically Programmable Fuse With Compressive-Stress Nitride Layer. IEEE Electron Device Letters, 2014, 35, 297-299.	3.9	4

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109	GaN-Based Light-Emitting Diodes With Staircase Electron Injector Structure. Journal of Display Technology, 2014, 10, 162-166.	1.2	3
110	UV Enhanced Emission Performance of Low Temperature Grown Ga-Doped ZnO Nanorods. IEEE Photonics Technology Letters, 2014, 26, 66-69.	2.5	24
111	Impact of Aluminum Ion Implantation on the Low Frequency Noise Characteristics of Hf-Based High-(k) /Metal Gate pMOSFETs. IEEE Electron Device Letters, 2014, 35, 954-956.	3.9	1
112	Amorphous InGaZnO Ultraviolet Phototransistors With a Thin Ga₂O₃ Layer. IEEE Journal of Selected Topics in Quantum Electronics, 2014, 20, 125-129.	2.9	14
113	Failure Mechanism for GaN-Based High-Voltage Light-Emitting Diodes. IEEE Photonics Technology Letters, 2014, 26, 1073-1076.	2.5	9
114	Characteristics of tantalum-doped silicon oxide-based resistive random access memory. Materials Science in Semiconductor Processing, 2014, 27, 293-296.	4.0	12
115	Synthesis of CZTSe nanoink via a facile one-pot heating route based on polyetheramine chelation. Solar Energy Materials and Solar Cells, 2014, 128, 156-165.	6.2	18
116	ZnO Branched Nanowires and the p-CuO/n-ZnO Heterojunction Nanostructured Photodetector. IEEE Nanotechnology Magazine, 2013, 12, 263-269.	2.0	62
117	Carbon Nanotubes With Adsorbed Au for Sensing Gas. IEEE Sensors Journal, 2013, 13, 2423-2427.	4.7	36
118	Method for Improving the Stability of Gen 5 Silicon Thin-film Tandem Solar Cell. IEEE Journal of Photovoltaics, 2013, 3, 1140-1143.	2.5	1
119	Synthesis of Cu2ZnSnSe4 nanocrystals from metal sources using a facile process in isophorondiamine. Materials Letters, 2013, 98, 71-73.	2.6	10
120	${m Ga}_{2}{m O}_{3}$ Nanowire Photodetector Prepared on ${m SiO}_{2}/{m Si}$ Template. IEEE Sensors Journal, 2013, 13, 2368-2373.	4.7	40
121	GaN-Based Light-Emitting Diodes With AlGaN Strain Compensation Buffer Layer. Journal of Display Technology, 2013, 9, 910-914.	1.2	3
122	Low-Frequency Noise Characteristics of In-Doped ZnO Ultraviolet Photodetectors. IEEE Photonics Technology Letters, 2013, 25, 2043-2046.	2.5	24
123	Low-Frequency Noise Characteristics of ZnO Nanorods Schottky Barrier Photodetectors. IEEE Sensors Journal, 2013, 13, 2115-2119.	4.7	26
124	GaN-Based LEDs With an HT-AlN Nucleation Layer Prepared on Patterned Sapphire Substrate. IEEE Photonics Technology Letters, 2013, 25, 88-90.	2.5	5
125	Electron-Field-Emission Properties of Gallium Compound by Ammonification of Ga <sub›2</sub›O$_{3}$ Nanowires. IEEE Nanotechnology Magazine, 2013, 12, 692-695.	2.0	1
126	$etahbox{-}{m Ga}_{2}{m O}_{3}$ Nanowires-Based Humidity Sensors Prepared on GaN/Sapphire Substrate. IEEE Sensors Journal, 2013, 13, 4891-4896.	4.7	11

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127	Different alkali carbonates on the microstructure and photoluminescence properties of BaY2ZnO5:Tb3+ phosphors prepared using the solid-state method. Journal of Physics and Chemistry of Solids, 2013, 74, 344-347.	4.0	17
128	GaN-Based Planar p-i-n Photodetectors With the Be-Implanted Isolation Ring. IEEE Transactions on Electron Devices, 2013, 60, 1178-1182.	3.0	14
129	Field-Emission and Photoelectrical Characteristics of Gaâ€“ZnO Nanorods Photodetector. IEEE Transactions on Electron Devices, 2013, 60, 1905-1910.	3.0	39
130	Recovery of thermal-degraded ZnO photodetector by embedding nano silver oxide nanoparticles. Applied Surface Science, 2013, 279, 31-35.	6.1	13
131	Embedded-Ge source and drain in InGaAs/GaAs dual channel MESFET. Current Applied Physics, 2013, 13, 1577-1580.	2.4	4
132	Numerical Simulation of GaN-Based LEDs With Chirped Multiquantum Barrier Structure. IEEE Journal of Quantum Electronics, 2013, 49, 436-442.	1.9	11
133	UV Enhanced Field Emission for Î²-Ga2O3 Nanowires. IEEE Electron Device Letters, 2013, 34, 701-703.	3.9	3
134	AlGaN/GaN high electron mobility transistors based on InGaN/GaN multi-quantum-well structures with photo-chemical vapor deposition of SiO2 dielectrics. Microelectronic Engineering, 2013, 104, 105-109.	2.4	8
135	Improved Field Emission Properties of Ag-Decorated Multi-Walled Carbon Nanotubes. IEEE Photonics Technology Letters, 2013, 25, 1017-1019.	2.5	18
136	Microstructure and photoluminescent properties of BaY2ZnO5:Tb3+ phosphors with addition of lithium carbonate. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2013, 178, 375-379.	3.5	9
137	InGaP/GaAs/Ge tripleâ€junction solar cells with ZnO nanowires. Progress in Photovoltaics: Research and Applications, 2013, 21, 1645-1652.	8.1	12
138	Optical and Structural Properties of Ga-Doped ZnO Nanorods. Journal of Nanoscience and Nanotechnology, 2013, 13, 8320-8324.	0.9	4
139	Effects of postdeposition annealing on a high-k-last/gate-last integration scheme for 20â€‰nm nMOS and pMOS. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2013, 31, 020604.	1.2	4
140	InN/GaN alternative growth of thick InGaN wells on GaN-based light emitting diodes. Optical Materials Express, 2013, 3, 1952.	3.0	7
141	GaN-Based Green-Light-Emitting Diodes with InN/GaN Growth-Switched InGaN Wells. Applied Physics Express, 2013, 6, 102101.	2.4	8
142	ZnO Nanowires Modified with Au Nanoparticles Exhibiting High Field-Emission Performance. ECS Journal of Solid State Science and Technology, 2013, 2, N149-N151.	1.8	7
143	Characterization of Oxide Traps in 28 nm n-Type Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistors with Different Uniaxial Tensile Stresses Utilizing Random Telegraph Noise. Japanese Journal of Applied Physics, 2013, 52, 04CC24.	1.5	4
144	Noise Properties of Fe-ZnO Nanorod Ultraviolet Photodetectors. IEEE Photonics Technology Letters, 2013, 25, 2089-2092.	2.5	16

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145	Effects of Initial GaN Growth Mode on Patterned Sapphire on the Opto-Electrical Characteristics of GaN-Based Light-Emitting Diodes. Journal of Display Technology, 2013, 9, 292-296.	1.2	7
146	UV Enhanced Indium-Doped ZnO Nanorod Field Emitter. IEEE Transactions on Electron Devices, 2013, 60, 3901-3906.	3.0	12
147	AlGaInP-Based LEDs With AuBe-Diffused AZO/GaP Current Spreading Layer. IEEE Journal of Quantum Electronics, 2013, 49, 846-851.	1.9	9
148	IMPROVEMENT IN THERMAL DEGRADATION OF ZnO PHOTODETECTOR BY EMBEDDING SILVER OXIDE NANOPARTICLES. Functional Materials Letters, 2013, 06, 1350001.	1.2	11
149	Synthesis and optical properties of ZnO thin films prepared by SILAR method with ethylene glycol. Advances in Nano Research, 2013, 1, 93-103.	0.9	6
150	Align Ag Nanorods via Oxidation Reduction Growth Using RF-Sputtering. Journal of Nanomaterials, 2012, 2012, 1-6.	2.7	5
151	GaN-based light-emitting diodes with embedded air void arrays. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2012, 30, 041207.	1.2	2
152	A $hbox{TiO}_{2}$ Nanowire MIS Photodetector With Polymer Insulator. IEEE Electron Device Letters, 2012, 33, 1577-1579.	3.9	15
153	GaN-Based Light-Emitting Diode With Sputtered AlN Nucleation Layer. IEEE Photonics Technology Letters, 2012, 24, 294-296.	2.5	49
154	A Visible-Blind TiO2Nanowire Photodetector. Journal of the Electrochemical Society, 2012, 159, J132-J135.	2.9	41
155	Microstructural Characteristics of InGaZnO Thin Film Using an Electrical Current Method. Materials Transactions, 2012, 53, 733-738.	1.2	3
156	GaN-Based LEDs with a Mirror Structure and an Insulating Layer. , 2012, , .		0
157	Enhanced Current Spreading for GaN-Based Side-View LEDs by Adding an Metallic Stripe Across the Long Side of the Chip. IEEE Photonics Technology Letters, 2012, 24, 1412-1414.	2.5	4
158	${m TiO}_{2}$ Nanowires UV Photodetectors With Ir Schottky Contacts. IEEE Photonics Technology Letters, 2012, 24, 1584-1586.	2.5	8
159	InGaN-Based Light-Emitting Diodes With an AlGaN Staircase Electron Blocking Layer. IEEE Photonics Technology Letters, 2012, 24, 1737-1740.	2.5	6
160	Deep UV ${m Ta}_{2}{m O}_{5}$/Zinc-Indium-Tin-Oxide Thin Film Photo-Transistor. IEEE Photonics Technology Letters, 2012, 24, 1018-1020.	2.5	23
161	Enhanced Field Electron Emission From Zinc-Doped CuO Nanowires. IEEE Electron Device Letters, 2012, 33, 887-889.	3.9	17
162	GaN-Based LEDs With Omnidirectional Metal Underneath an Insulating ${m SiO}_{2}$ Layer. IEEE Photonics Technology Letters, 2012, 24, 815-817.	2.5	8

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163	Effect of temperature on the deposition of ZnO thin films by successive ionic layer adsorption and reaction. Applied Surface Science, 2012, 258, 8109-8116.	6.1	22
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